



2822

PATENT
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12/10 Amdt

12-23-02

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: 09/744,877
Filed: January 29, 2001
Inventor(s):
Halimaoui, Aomar

Title: PROCESS FOR FORMING
AN OXIDE LAYER OF
NON-UNIFORM
THICKNESS ON THE
SURFACE OF A SILICON
SUBSTRATE

Examiner: Novacek, Christy L
Group/Art Unit: 2822
Atty. Dkt. No: 5310-03000

CERTIFICATE OF MAILING
UNDER 37 C.F.R. §1.8

DATE OF DEPOSIT: 12-4-02

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail on the date indicated above and is addressed to:
Commissioner for Patents
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Jackie L. Pitre
Jackie L. Pitre

SUPPLEMENTAL AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Amendment

Sir:

Please amend the above-captioned application as follows:

In the Claims:

Please amend the claims as follows:

33. (Amended) A process for forming a semiconductor device comprising a plurality of MOS transistors at predetermined regions of a silicon substrate, comprising: